



Phase Control Thyristor

DS5819-4 February 2014 (LN31295)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{DRM} and V _{RRM} V	Conditions
DCR3640W52* DCR3640W50 DCR3640W48 DCR3640W46	5200 5000 4800 4600	$\begin{split} T_{vj} = -40^{\circ}\text{C to } 125^{\circ}\text{C}, \\ I_{DRM} = I_{RRM} = 300\text{mA}, \\ V_{DRM}, V_{RRM} t_p = 10\text{ms}, \\ V_{DSM} \& V_{RSM} = \\ V_{DRM} \& V_{RRM} + 100V \\ respectively \end{split}$

Lower voltage grades available. 5000V @ -40° C, 5200V @ 0°C

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR3640W52

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

V_{DRM}	5200V
I _{T(AV)}	3550A
ITSM	49000A
dV/dt*	1500V/µs
dl/dt	400A/μs

* Higher dV/dt selections available

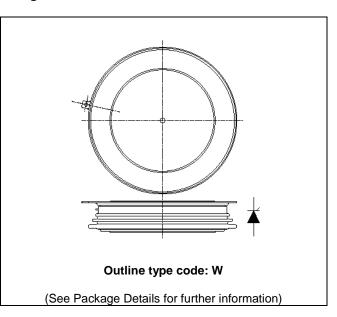


Fig. 1 Package outline



CURRENT RATINGS

$T_{case} = 60$ °C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
I _{T(AV)}	Mean on-state current	Half wave resistive load	3550	А
I _{T(RMS)}	RMS value	-	5576	А
lτ	Continuous (direct) on-state current	-	5240	А

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 125°C	49	kA
l ² t	I ² t for fusing	$V_R = 0$	12.0	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	DC	-	0.00631	°C/W
		Single side cooled	Anode DC	-	0.01115	°C/W
			Cathode DC	-	0.01453	°C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Clamping force 76kN	Double side	-	0.0014	°C/W
		(with mounting compound)	Single side	-	0.0028	°C/W
T_{vj}	Virtual junction temperature	Blocking V _{DRM} / _{VRRM}		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
Fm	Clamping force			68.0	84.0	kN





DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditio	ns	Min.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	300	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V_{DRM} , $T_j = 125$ °C, ga	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% V _{DRM} to 2x I _{T(AV)}	Repetitive 50Hz	-	200	A/µs
		Gate source 30V, 10Ω , $t_r < 0.5\mu s$, $T_i = 125^{\circ}C$	Non-repetitive	-	400	A/µs
V	Throshold voltage I ow level	,	<u> </u>	_	0.86	V
$V_{T(TO)}$	Threshold voltage – Low level	500A to 1700A at T _{case} = 125		-	0.86	V
	Threshold voltage – High level	1700A to 5000A at T _{case} = 12	25°C	-	0.98	V
r _T	On-state slope resistance – Low level	500A to 1700A at T _{case} = 125°C		-	0.2533	mΩ
	On-state slope resistance – High level	1700A to 5000A at T _{case} = 125°C		-	0.1886	mΩ
t _{gd}	Delay time	$V_D = 67\% \ V_{DRM}$, gate source 30V, 10Ω $t_r = 0.5 \mu s$, $T_j = 25^{\circ} C$		-	3	μs
t _q	Turn-off time	$T_j = 125$ °C, $V_R = 200$ V, $dI/dt = 1$ A/µs, $dV_{DR}/dt = 20$ V/µs linear		400	750	μs
Qs	Stored charge	$I_T = 2000A$, $T_j = 125$ °C, $dI/dt - 1A/\mu s$,		2700	6325	μC
IL	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	А
l _H	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 500$	0A, I _T = 5A	-	300	mA





GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V_{GT}	Gate trigger voltage	V _{DRM} = 5V, T _{case} = 25°C	1.5	V
V_{GD}	Gate non-trigger voltage	At 50% V _{DRM} , T _{case} = 125°C	0.4	V
I _{GT}	Gate trigger current	V _{DRM} = 5V, T _{case} = 25°C	400	mA
I _{GD}	Gate non-trigger current	At 50% V _{DRM} , T _{case} = 125°C	15	mA

CURVES

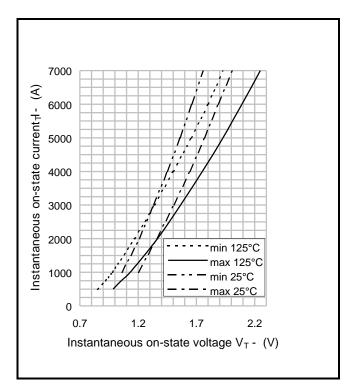


Fig.2 Maximum & minimum on-state characteristics

 V_{TM} **EQUATION** Where A = 0.722818

B = -0.002455

 $V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T}$ C = 0.000096

D = 0.010486

these values are valid for $T_j = 125$ °C for $I_T 100A$ to 7000A

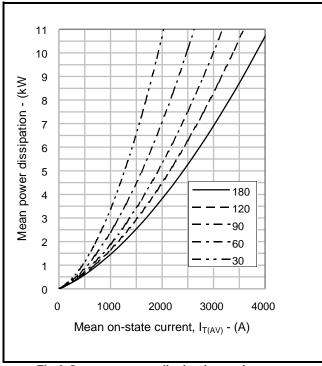


Fig.3 On-state power dissipation – sine wave

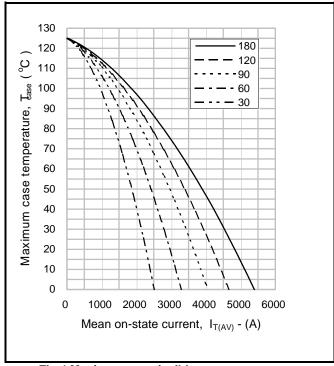


Fig.4 Maximum permissible case temperature, double side cooled – sine wave

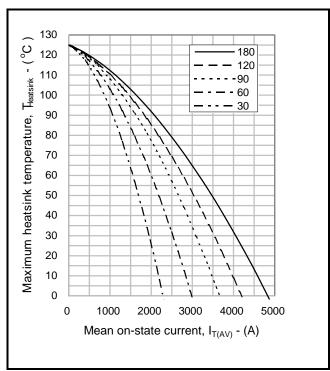


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

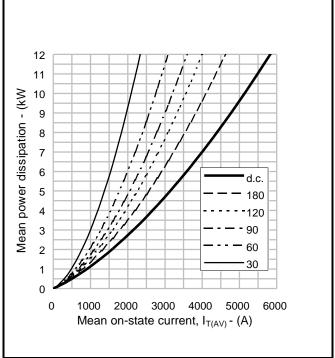


Fig.6 On-state power dissipation - rectangular wave



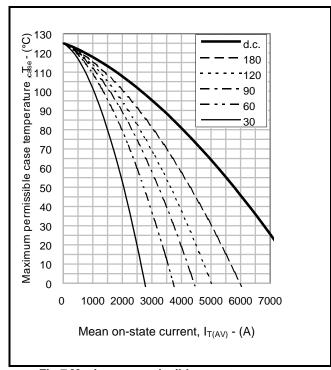


Fig.7 Maximum permissible case temperature, double side cooled – rectangular wave

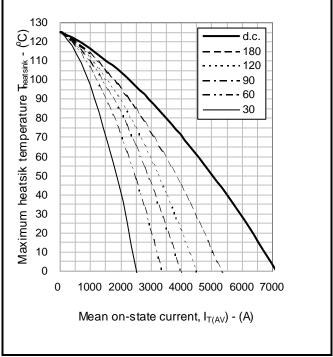
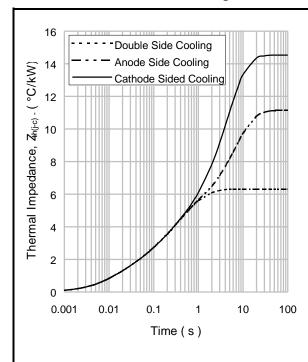


Fig.8 Maximum permissible heatsink temperature, double side cooled – rectangular wave



		1	2	3	4
Double side cooled	R _i (°C/kW)	0.8816	1.2993	2.8048	1.3305
	T _i (s)	0.0106818	0.058404	0.3584979	1.1285
Anode side cooled	R _i (°C/kW)	1.5197	3.2398	5.7622	0.6312
	T _i (s)	0.0170581	0.2424644	6.013	15.364
Cathode side cooled	R _i (°C/kW)	1.4106	2.4667	6.7451	3.9054
	T _i (s)	0.0158344	0.1786951	3.6201	6.196

 $Z_{th} = \sum [R_i x (1-exp. (t/t_i))]$ [1]

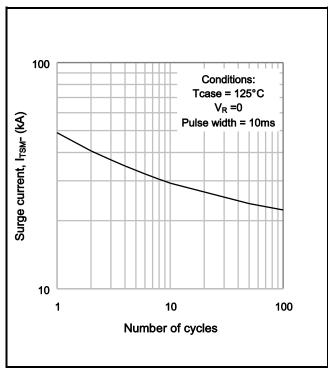
 $\Delta R_{\text{th(j-c)}}$ Conduction

Tables show the increments of thermal resistance $R_{\text{th}(j\text{-}c)}$ when the device operates at conduction angles other than d.c.

Double side cooling				Anode Side Cooling				
	ΔZ_{th} ($\Delta Z_{th}(z)$			Δ^{Z}	th (z)		
θ°	sine.	rect.		θ°	sine.	rect.		
180	1.00	0.67		180	0.94	0.64		
120	1.16	0.97		120	1.08	0.91		
90	1.33	1.13		90	1.23	1.06		
60	1.48	1.31		60	1.37	1.22		
30	1.61 1.51			30	1.47	1.38		
				45	4.50			

Sa	thode Sided Cooling			
	$\Delta Z_{th}(z)$			
θ°	sine.	rect.		
180	0.95	0.65		
120	1.09	0.92		
90	1.25	1.07		
60	1.38	1.23		
30	1.49	1.40		
4.5	4.54	4.40		

Fig.9 Maximum (limit) transient thermal impedance – junction to case (°C/kW)



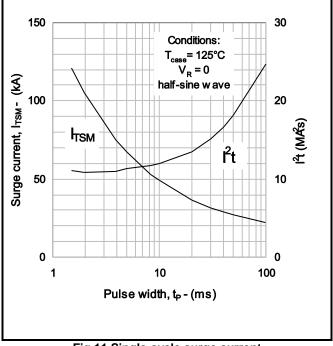


Fig.10 Multi-cycle surge current

Fig.11 Single-cycle surge current

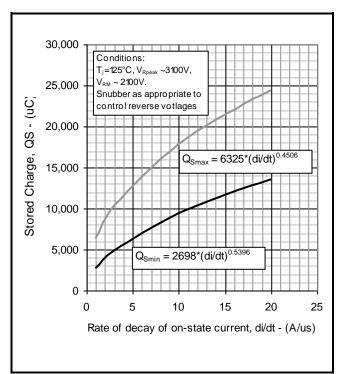


Fig.12 Stored Charge

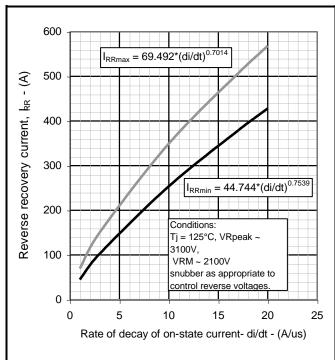


Fig.13 Reverse recovery current

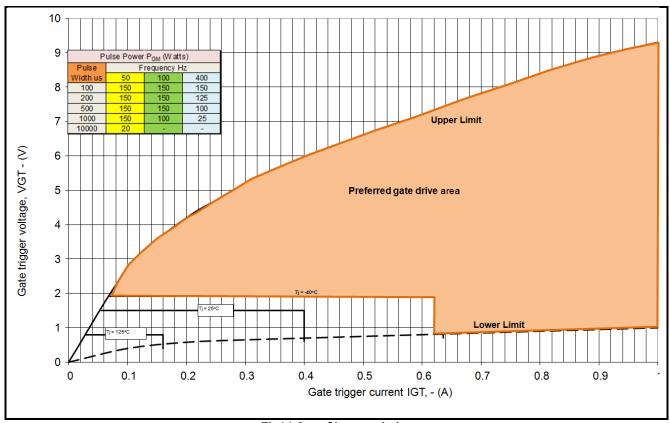


Fig14 Gate Characteristics

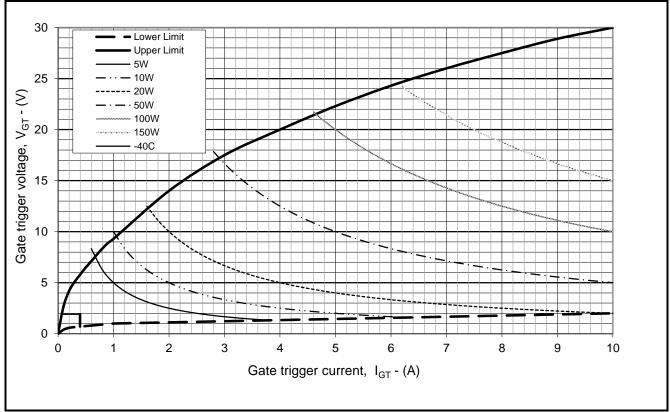


Fig. 15 Gate characteristics



PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

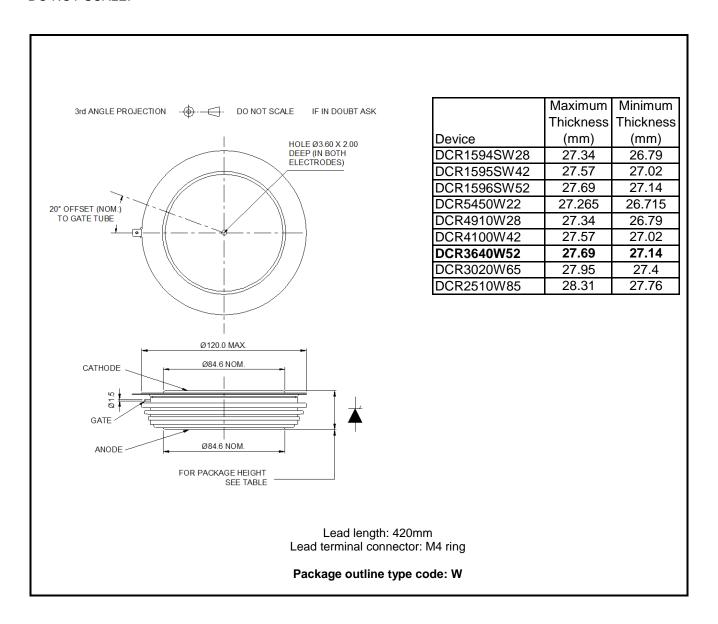


Fig.16 Package outline





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